



CHENMKO ENTERPRISE CO.,LTD

Halogen free devices

**SURFACE MOUNT
SWITCHING DIODE**

VOLTAGE 350 Volts CURRENT 225 mAmpere

CHBD3004GP

APPLICATION

- * Ultra high speed switching

FEATURE

- * Small surface mounting type. (SOT-23)
- * High speed. (TRR=50 nSec Typ.)
- * Suitable for high packing density.
- * Maximum total power dissipation is 350mW.
- * Peak forward current is 625mA.
- * High voltage capability.

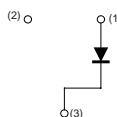
CONSTRUCTION

- * Silicon epitaxial planar

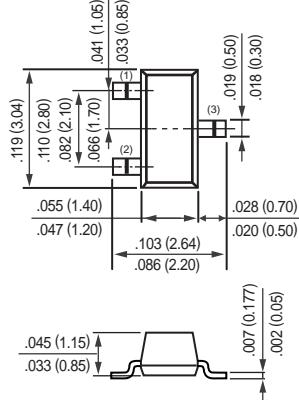
MARKING

- * LD6

CIRCUIT



SOT-23



Dimensions in millimeters

SOT-23

MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	CHBD3004GP	UNITS
Maximum Recurrent Peak Reverse Voltage	VR _{RM}	350	Volts
Maximum RMS Voltage	VR _M S	212	Volts
Maximum DC Blocking Voltage	V _D C	300	Volts
Maximum Average Forward Rectified Current	I _O	225	mAmps
Peak Forward Surge Current	I _{FSM}	4.0 1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	C _J	5.0	pF
Maximum Reverse Recovery Time (Note 2)	TRR	50	nSec
Typical Thermal Resistance	R _{θJA}	357	°C/W
Operation and Storage Temperature Range	T _{J,TSTG}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CHBD3004GP	UNITS
Reverse Breakdown Voltage at I _R = 150μA	BV _R	350 Min.	Volts
Maximum Instantaneous Forward Voltage at I _F = 100mA	V _F	1.0	Volts
Maximum Average Reverse Current at V _R = 240V	I _R	100	nAmps
		100	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0 volts.

2. Measured at applied forward current of 30mA ,reverse current of 30mA ,R_L=100 Ω and recovery to I_{RR}=3mA.

3. ESD sensitive product handling required.

2004-09

RATING CHARACTERISTIC CURVES (CHBD3004GP)

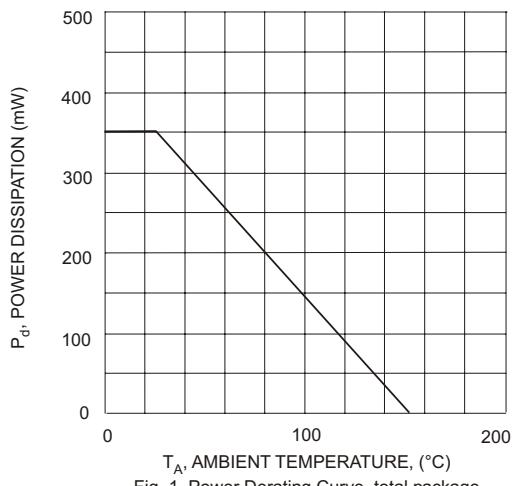


Fig. 1 Power Derating Curve, total package

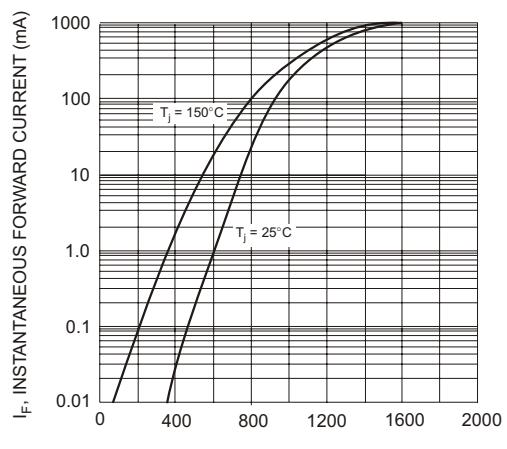


Fig. 2 Typical Forward Characteristics, per element

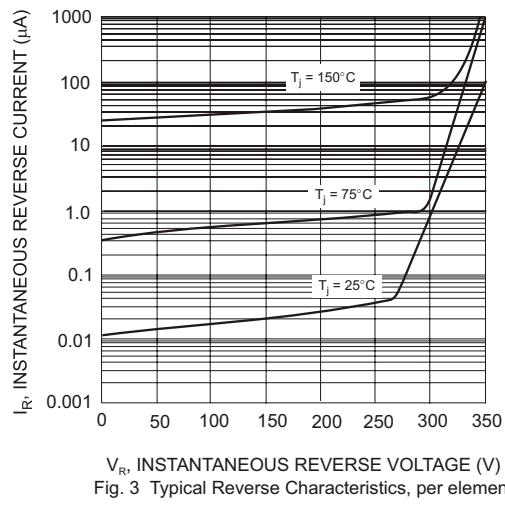


Fig. 3 Typical Reverse Characteristics, per element

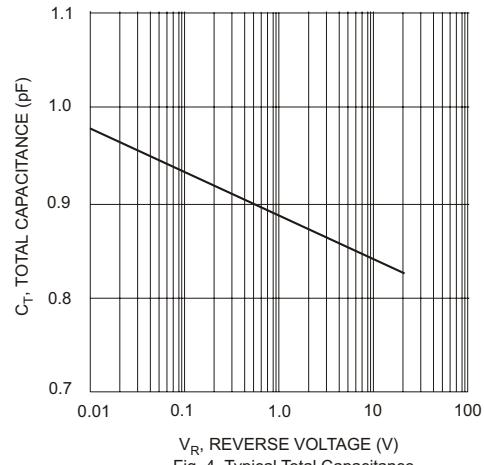


Fig. 4 Typical Total Capacitance vs. Reverse Voltage, per element